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GVGR-T10GD

- **PN-type Photodiode**
- **Indium Gallium Nitride Based Material**
- **300 – 510 nm**
- **Photovoltaic Operation Mode**
- **TO-46 Package**

RoHS COMPLIANT

Description

GVRG-T10GD is a Photodiode working in the spectral range of 300 – 510 nm. It contains an Indium Gallium Nitride based chip die, housed into TO-46 package. It is a great solution, as example for applications like blue LED monitoring, UV curing or UV LED monitoring.

Absolute Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse Voltage	V_R	5	V
Forward Current	I_{OP}	1	mA
Operating Temperature	T_{CASE}	-30 – +85	°C
Storage Temperature	T_{STG}	-40 – +90	°C
Soldering Temperature *	T_{SLD}	260	°C

* must be completed within 10 seconds

Electro-Optical Characteristics

T_{CASE} = 25°C

Parameter	Symbol	Values	Unit
Dark Current (V_R=0.1V)	I_D	max. 1	nA
Photo Current (LED 405nm, 1mW/cm^2)	I_{PH}	typ. 11	nA
Temperature Coefficient	T_C	Typ. -0.08	%/°C
Responsivity (405nm, V_R=0V)	R	typ. 0.026	A/W
Spectral Detection Range	λ	300 – 510	nm
Active Area	A		mm^2

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Outline Dimensions

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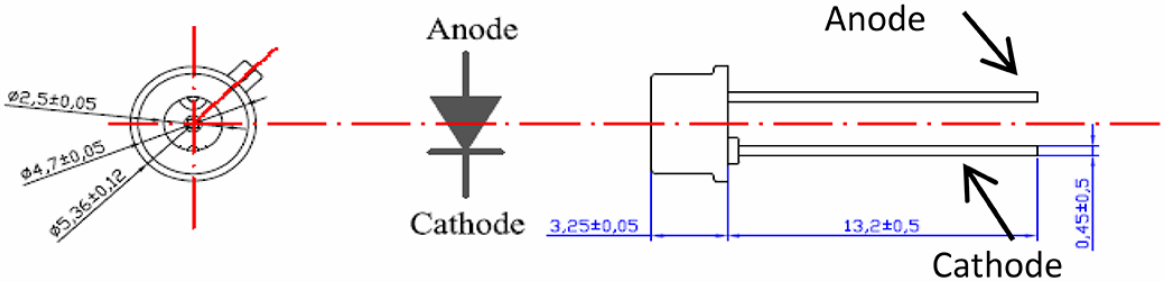
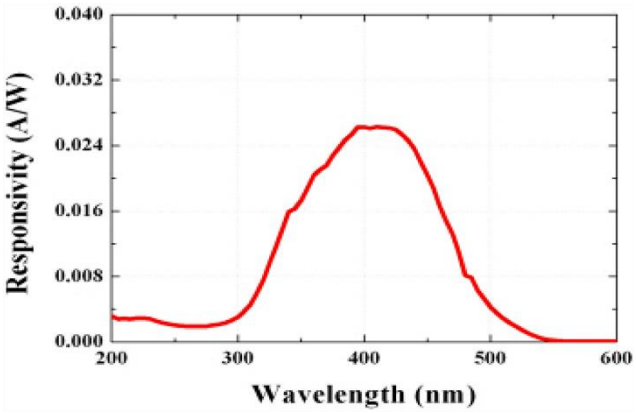
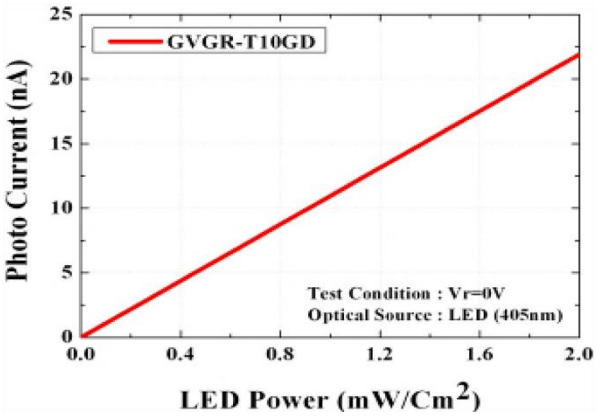


Typical Performance Curves

Relative Responsivity



Photocurrent along LED Power



Caution

ESD can damage the device hence please avoid ESD.